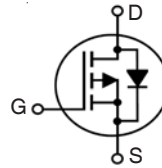


# TrenchP™ Power MOSFET

**IXTT76P10THV**  
**IXTA76P10T**  
**IXTP76P10T**  
**IXTH76P10T**

$V_{DSS} = -100V$   
 $I_{D25} = -76A$   
 $R_{DS(on)} \leq 25m\Omega$

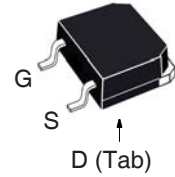
P-Channel Enhancement Mode  
Avalanche Rated



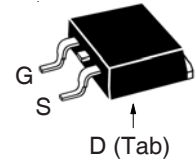
Symbol	Test Conditions	Maximum Ratings	
$V_{DSS}$	$T_J = 25^\circ C$ to $150^\circ C$	- 100	V
$V_{DGR}$	$T_J = 25^\circ C$ to $150^\circ C$ , $R_{GS} = 1M\Omega$	- 100	V
$V_{GSS}$	Continuous	$\pm 15$	V
$V_{GSM}$	Transient	$\pm 25$	V
$I_{D25}$	$T_C = 25^\circ C$	- 76	A
$I_{DM}$	$T_C = 25^\circ C$ , Pulse Width Limited by $T_{JM}$	- 230	A
$I_A$	$T_C = 25^\circ C$	- 38	A
$E_{AS}$	$T_C = 25^\circ C$	1	J
$P_D$	$T_C = 25^\circ C$	298	W
$T_J$		-55 ... +150	$^\circ C$
$T_{JM}$		150	$^\circ C$
$T_{stg}$		-55 ... +150	$^\circ C$
$T_L$	Maximum Lead Temperature for Soldering	300	$^\circ C$
$T_{SOLD}$	1.6 mm (0.062in.) from Case for 10s	260	$^\circ C$
$M_d$	Mounting Torque (TO-220 & TO-247)	1.13 / 10	Nm/lb.in.
<b>Weight</b>	TO-263	2.5	g
	TO-220	3.0	g
	TO-268HV	4.0	g
	TO-247	6.0	g

Symbol	Test Conditions ( $T_J = 25^\circ C$ , Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$BV_{DSS}$	$V_{GS} = 0V$ , $I_D = -250\mu A$	-100		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = -250\mu A$	- 2.0		- 4.0 V
$I_{GSS}$	$V_{GS} = \pm 15V$ , $V_{DS} = 0V$			$\pm 100$ nA
$I_{DSS}$	$V_{DS} = V_{DSS}$ , $V_{GS} = 0V$ $T_J = 125^\circ C$			- 15 $\mu A$
				- 750 $\mu A$
$R_{DS(on)}$	$V_{GS} = -10V$ , $I_D = 0.5 \cdot I_{D25}$ , Note 1			25 m $\Omega$

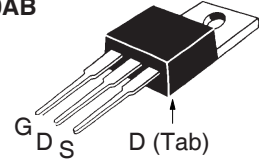
TO-268HV  
(IXTT)



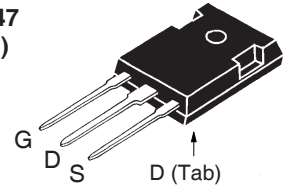
TO-263 AA  
(IXTA)



TO-220AB  
(IXTP)



TO-247  
(IXTH)



G = Gate      D = Drain  
S = Source    Tab = Drain

### Features

- International Standard Packages
- Avalanche Rated
- Extended FBSOA
- Fast Intrinsic Diode
- Low  $R_{DS(ON)}$  and  $Q_G$

### Advantages

- Easy to Mount
- Space Savings

### Applications

- High-Side Switching
- Push Pull Amplifiers
- DC Choppers
- Automatic Test Equipment
- Current Regulators
- Battery Charger Applications

Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ , Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$g_{fs}$	$V_{DS} = -10\text{V}$ , $I_D = 0.5 \cdot I_{D25}$ , Note 1	35	58	S
$C_{iss}$ $C_{oss}$ $C_{rss}$	$V_{GS} = 0\text{V}$ , $V_{DS} = -25\text{V}$ , $f = 1\text{MHz}$		13.7	nF
			890	pF
			275	pF
$t_{d(on)}$ $t_r$ $t_{d(off)}$ $t_f$	<b>Resistive Switching Times</b> $V_{GS} = -10\text{V}$ , $V_{DS} = 0.5 \cdot V_{DSS}$ , $I_D = 0.5 \cdot I_{D25}$ $R_G = 1\Omega$ (External)		25	ns
			40	ns
			52	ns
			20	ns
$Q_{g(on)}$ $Q_{gs}$ $Q_{gd}$	$V_{GS} = -10\text{V}$ , $V_{DS} = 0.5 \cdot V_{DSS}$ , $I_D = 0.5 \cdot I_{D25}$		197	nC
			65	nC
			65	nC
$R_{thJC}$ $R_{thCS}$	TO-220 TO-247			0.42 $^\circ\text{C/W}$
			0.50 0.21	$^\circ\text{C/W}$ $^\circ\text{C/W}$

#### Source-Drain Diode

Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ , Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$I_S$	$V_{GS} = 0\text{V}$			- 76 A
$I_{SM}$	Repetitive, Pulse Width Limited by $T_{JM}$			- 304 A
$V_{SD}$	$I_F = -38\text{A}$ , $V_{GS} = 0\text{V}$ , Note 1			-1.3 V
$t_{rr}$ $Q_{RM}$ $I_{RM}$	$I_F = -38\text{A}$ , $-di/dt = -100\text{A}/\mu\text{s}$ $V_R = -50\text{V}$ , $V_{GS} = 0\text{V}$		70	ns
			215	nC
			- 6	A

Note 1: Pulse test,  $t \leq 300\mu\text{s}$ , duty cycle,  $d \leq 2\%$ .

IXYS Reserves The Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:

4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
4,860,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

Fig. 1. Output Characteristics @  $T_J = 25^\circ\text{C}$

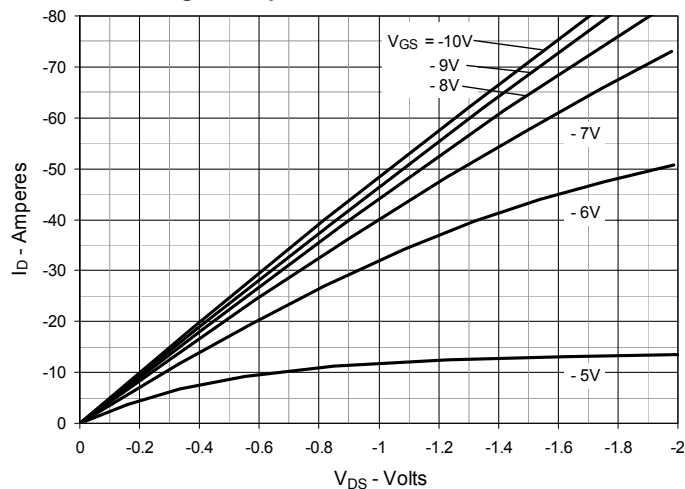


Fig. 2. Extended Output Characteristics @  $T_J = 25^\circ\text{C}$

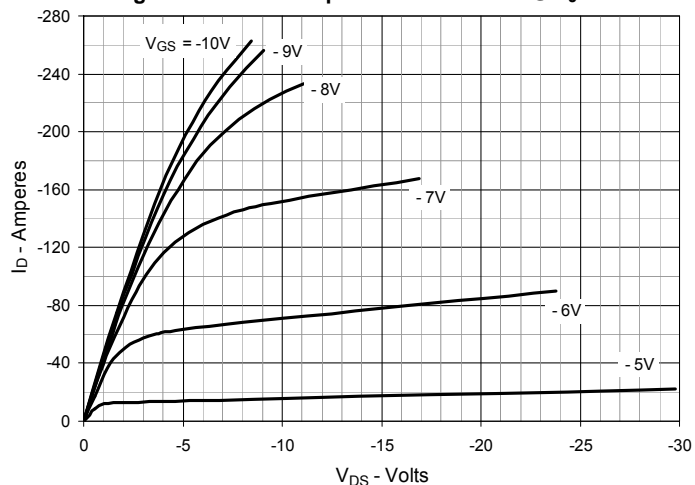


Fig. 3. Output Characteristics @  $T_J = 125^\circ\text{C}$

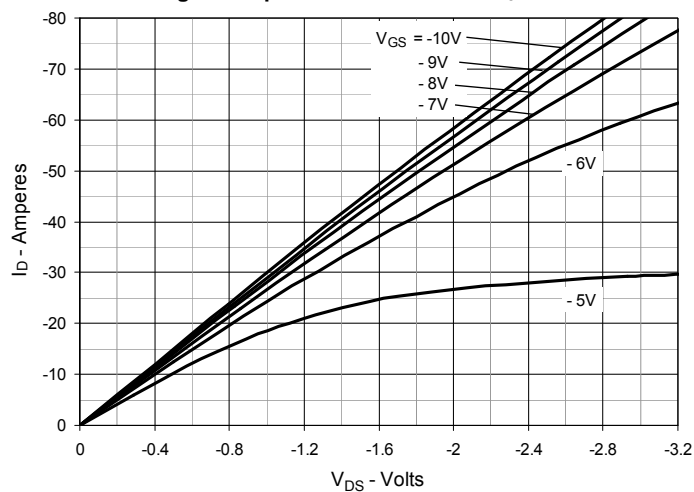


Fig. 4.  $R_{DS(on)}$  Normalized to  $I_D = -38\text{A}$  Value vs. Junction Temperature

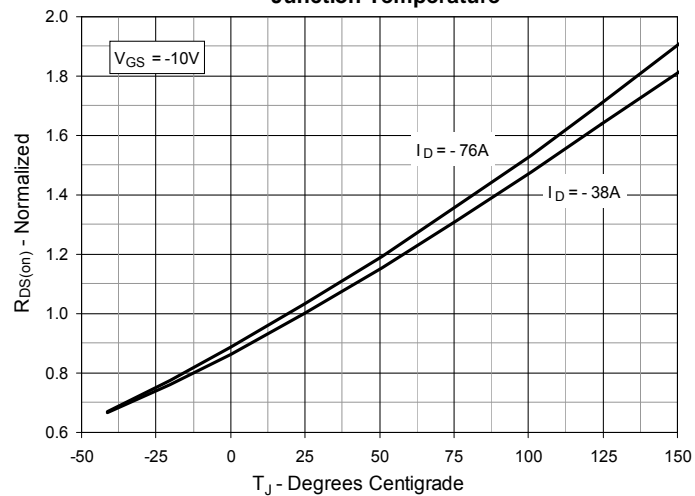


Fig. 5.  $R_{DS(on)}$  Normalized to  $I_D = -38\text{A}$  Value vs. Drain Current

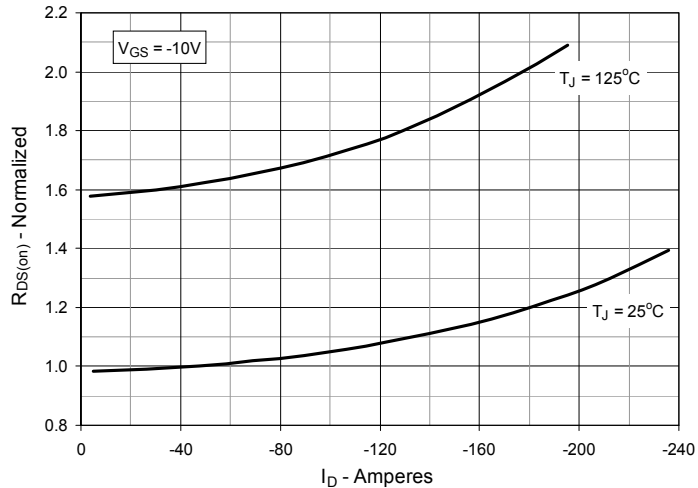


Fig. 6. Maximum Drain Current vs. Case Temperature

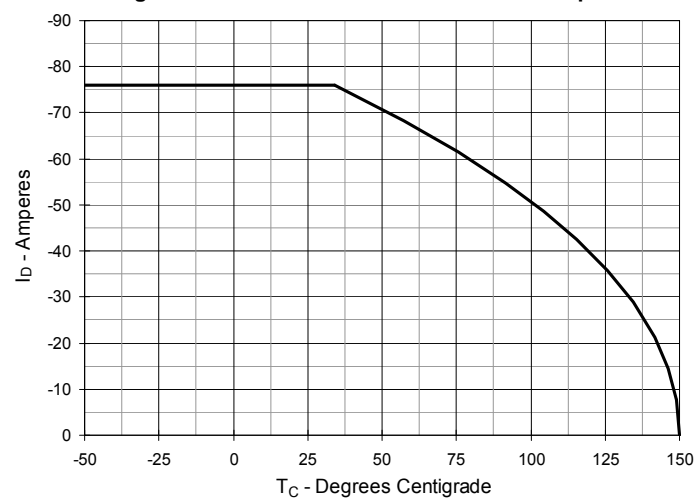


Fig. 7. Input Admittance

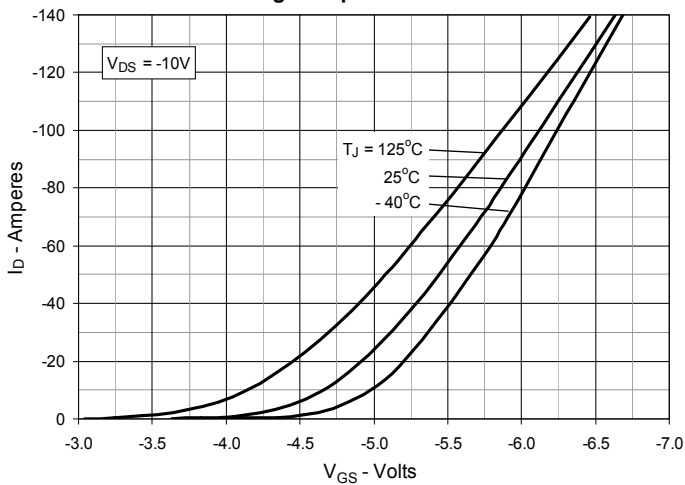


Fig. 8. Transconductance

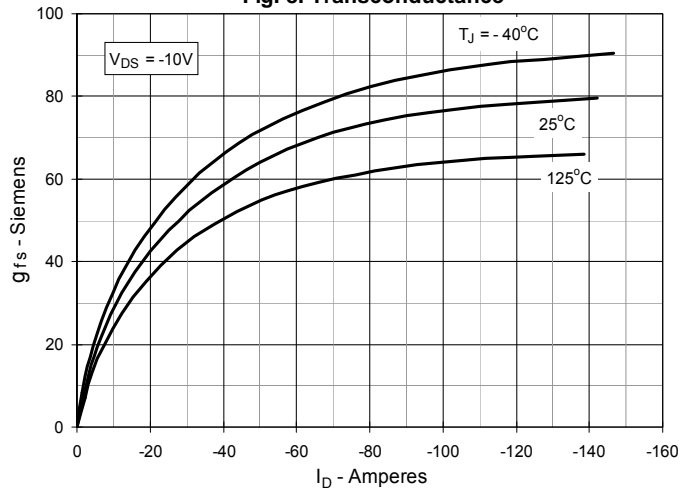


Fig. 9. Forward Voltage Drop of Intrinsic Diode

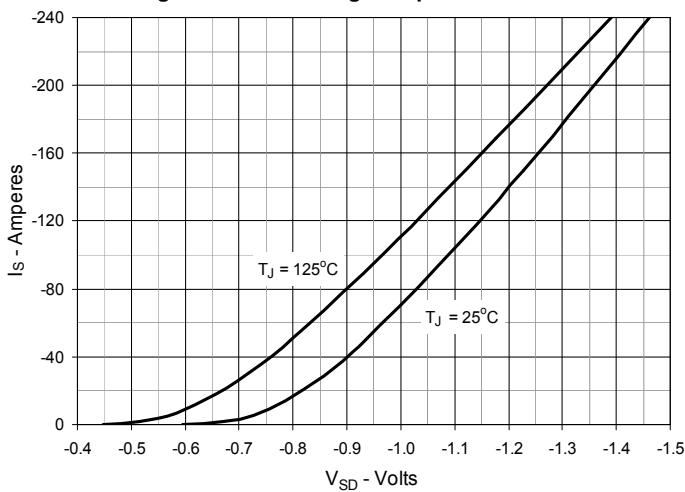


Fig. 10. Gate Charge

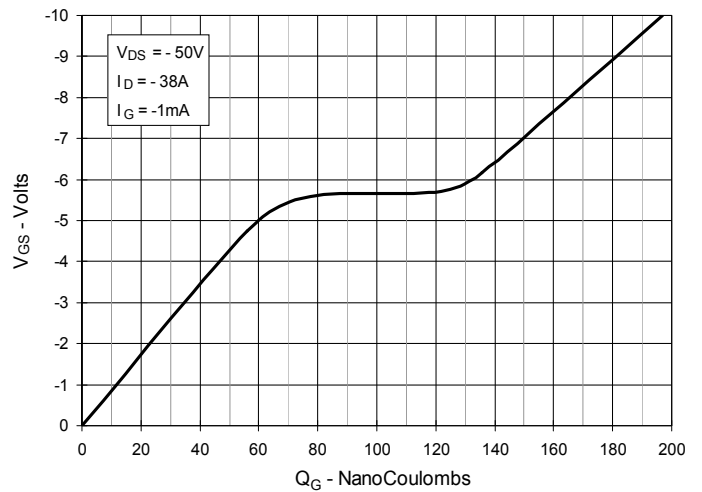


Fig. 11. Capacitance

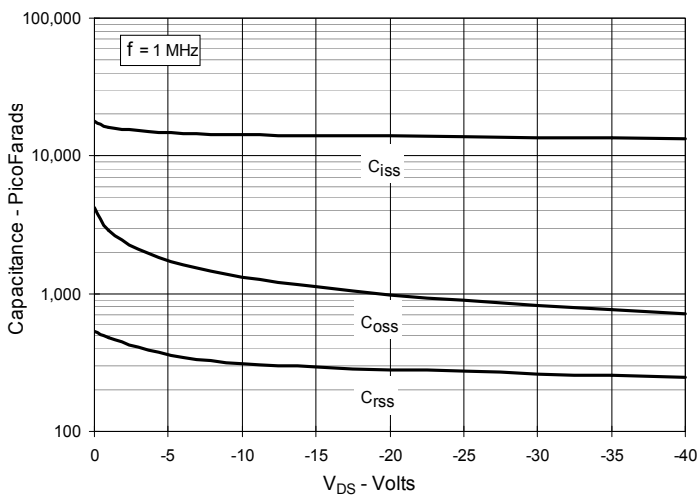
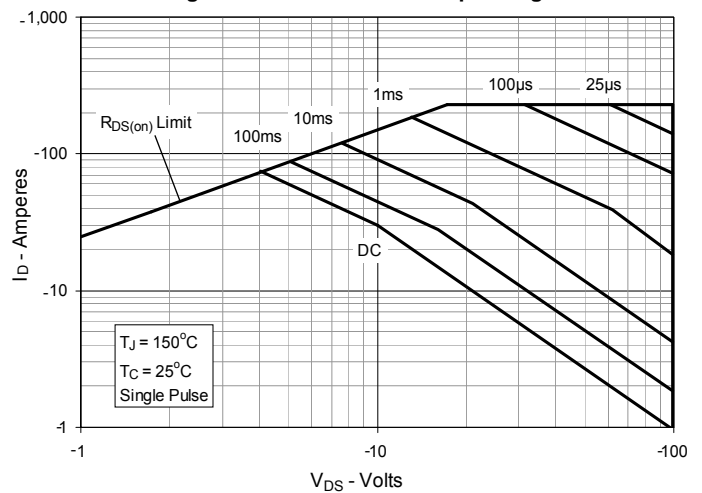
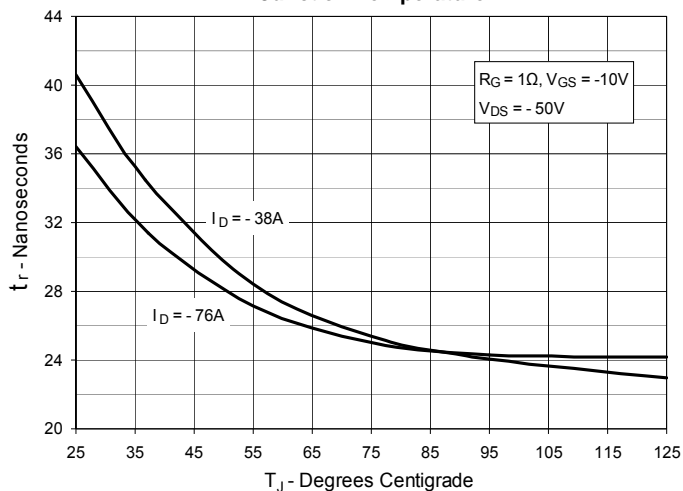


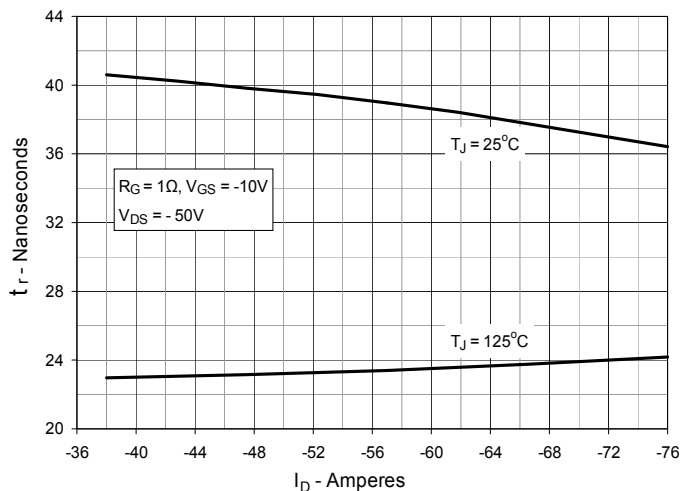
Fig. 12. Forward-Bias Safe Operating Area



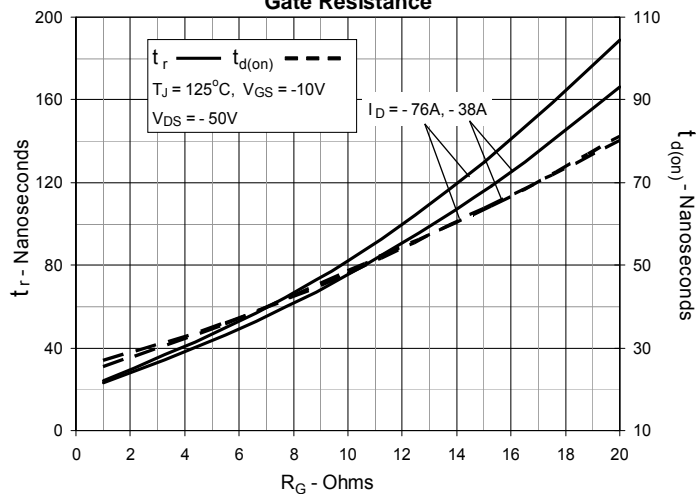
**Fig. 13. Resistive Turn-on Rise Time vs. Junction Temperature**



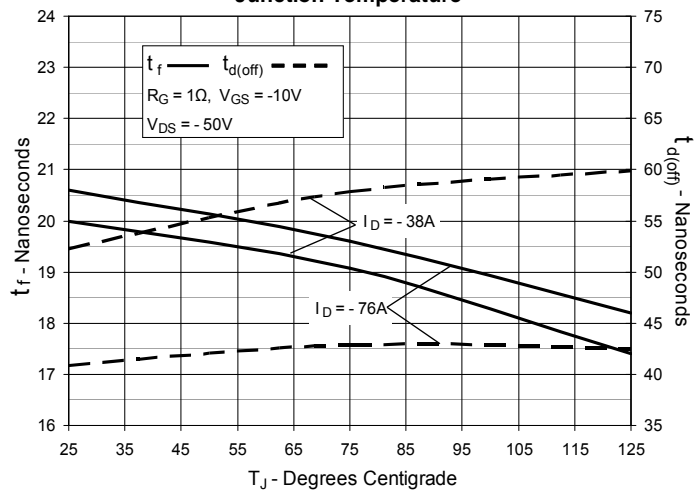
**Fig. 14. Resistive Turn-on Rise Time vs. Drain Current**



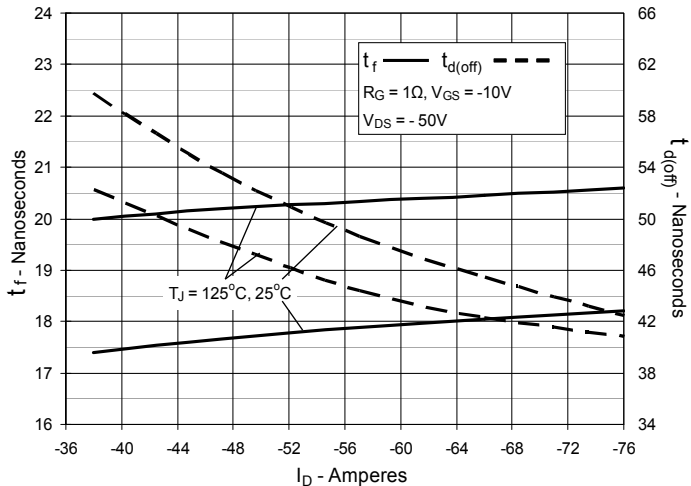
**Fig. 15. Resistive Turn-on Switching Times vs. Gate Resistance**



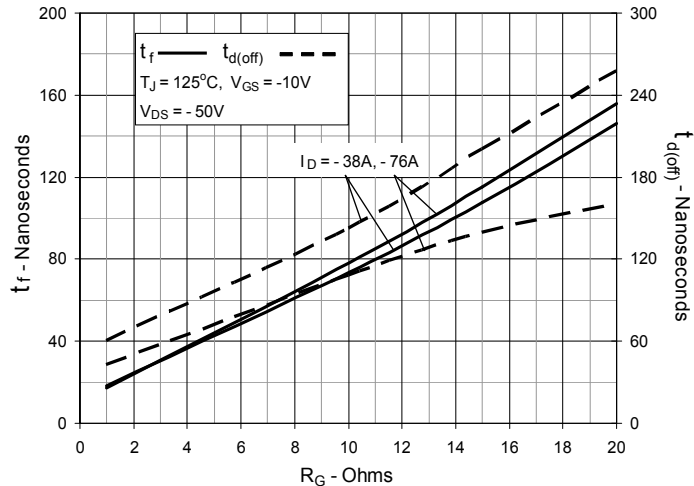
**Fig. 16. Resistive Turn-off Switching Times vs. Junction Temperature**



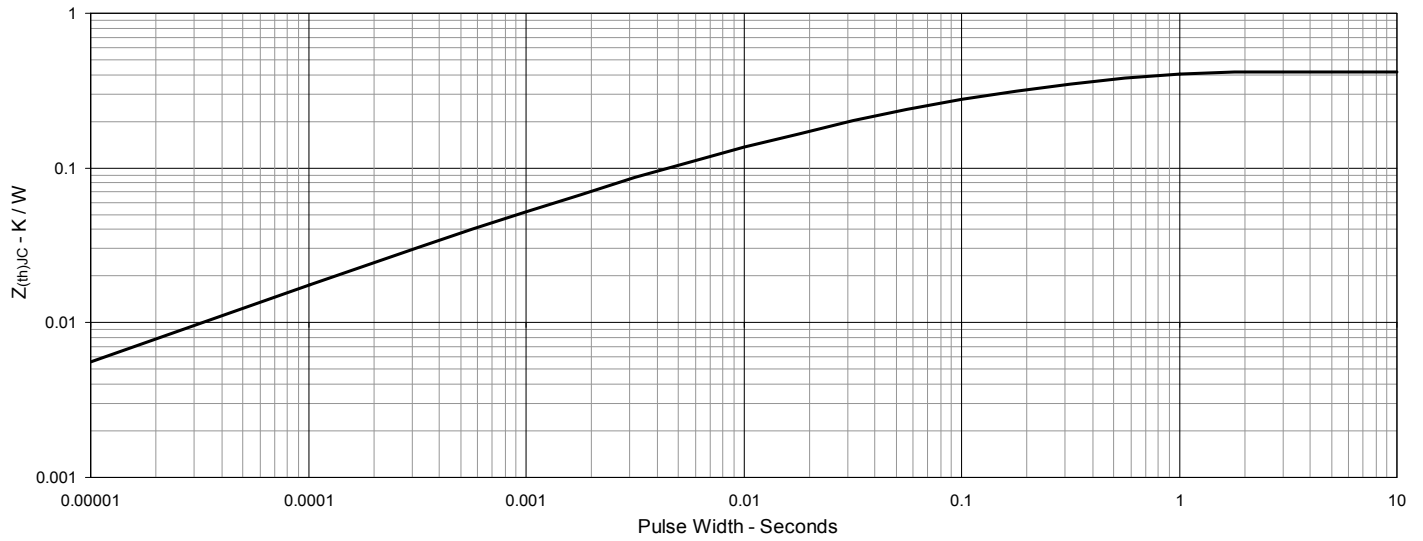
**Fig. 17. Resistive Turn-off Switching Times vs. Drain Current**



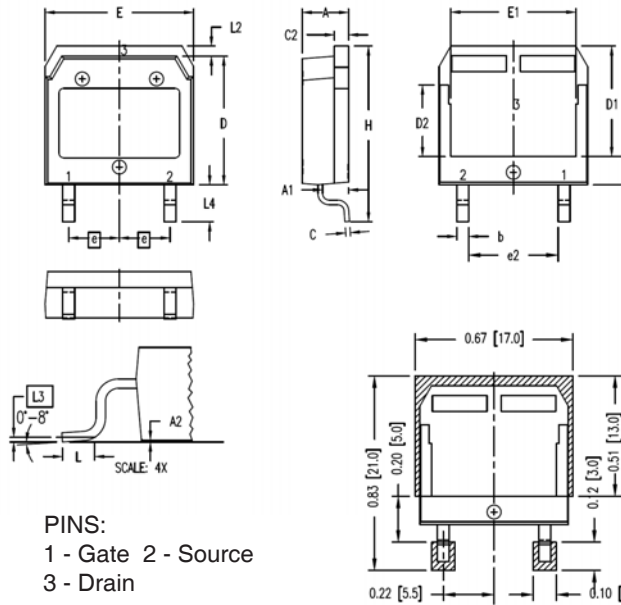
**Fig. 18. Resistive Turn-off Switching Times vs. Gate Resistance**



**Fig. 19. Maximum Transient Thermal Impedance**



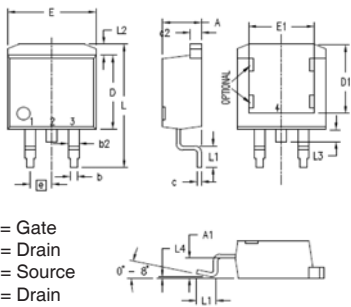
## TO-268HV Outline



**PINS:**  
 1 - Gate 2 - Source  
 3 - Drain

SYM	INCHES		MILLIMETER	
	MIN	MAX	MIN	MAX
A	.193	.201	4.90	5.10
A1	.106	.114	2.70	2.90
A2	.001	.010	0.02	0.25
b	.045	.057	1.15	1.45
C	.016	.026	0.40	0.65
C2	.057	.063	1.45	1.60
D	.543	.551	13.80	14.00
D1	.465	.476	11.80	12.10
D2	.295	.307	7.50	7.80
D3	.114	.126	2.90	3.20
E	.624	.632	15.85	16.05
E1	.524	.535	13.30	13.60
e	.215 BSC		5.45 BSC	
(e2)	.374	.386	9.50	9.80
H	.736	.752	18.70	19.10
L	.067	.079	1.70	2.00
L2	.039	.045	1.00	1.15
L3	.010 BSC		0.25 BSC	
L4	.150	.161	3.80	4.10

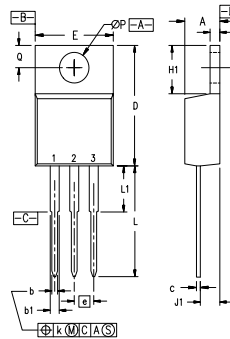
## TO-263 Outline



1 = Gate  
 2 = Drain  
 3 = Source  
 4 = Drain

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.160	.190	4.06	4.83
A1	.080	.110	2.03	2.79
b	.020	.039	0.51	0.99
b2	.045	.055	1.14	1.40
c	.016	.029	0.40	0.74
c2	.045	.055	1.14	1.40
D	.340	.380	8.64	9.65
D1	.315	.350	8.00	8.89
E	.380	.410	9.65	10.41
E1	.245	.320	6.22	8.13
e	.100 BSC		2.54 BSC	
L	.575	.625	14.61	15.88
L1	.090	.110	2.29	2.79
L2	.040	.055	1.02	1.40
L3	.050	.070	1.27	1.78
L4	0	.005	0	0.13

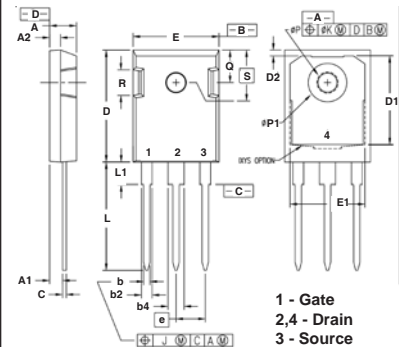
## TO-220 Outline



Pins: 1 - Gate 2 - Drain  
 3 - Source

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.170	.190	4.32	4.83
b	.025	.040	0.64	1.02
b1	.045	.065	1.15	1.65
c	.014	.022	0.35	0.56
D	.580	.630	14.73	16.00
E	.390	.420	9.91	10.66
e	.100 BSC		2.54 BSC	
F	.045	.055	1.14	1.40
H1	.230	.270	5.85	6.85
J1	.090	.110	2.29	2.79
k	0	.015	0	0.38
L	.500	.550	12.70	13.97
L1	.110	.230	2.79	5.84
ØP	.139	.161	3.53	4.08
Q	.100	.125	2.54	3.18

## TO-247 Outline



1 - Gate  
 2,4 - Drain  
 3 - Source

Dim.	Millimeter		Inches	
	min	max	min	max
A	4.70	5.30	0.185	0.209
A1	2.21	2.59	0.087	0.102
A2	1.50	2.49	0.059	0.098
b	0.99	1.40	0.039	0.055
b2	1.65	2.39	0.065	0.094
b4	2.59	3.43	0.102	0.135
c	0.38	0.89	0.015	0.035
D	20.79	21.45	0.819	0.845
D1	13.07	-	0.515	-
D2	0.51	1.35	0.020	0.053
E	15.48	16.24	0.610	0.640
E1	13.45	-	0.53	-
E2	4.31	5.48	0.170	0.216
e	5.45 BSC		0.215 BSC	
L	19.80	20.30	0.078	0.800
L1	-	4.49	-	0.177
Ø P	3.55	3.65	0.140	0.144
Ø P1	-	7.39	-	0.290
Q	5.38	6.19	0.212	0.244
S	6.14 BSC		0.242 BSC	



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